

3V 900MHZ LINEAR POWER AMPLIFIER MODULE

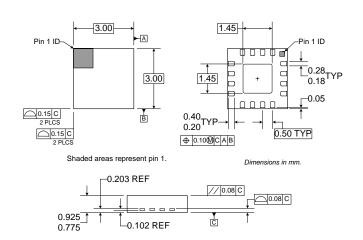
RoHS Compliant & Pb-Free Product

Typical Applications

- 3V CDMA/AMPS Cellular Handset
- 3V CDMA2000/1XRTT Cellular Handset
- 3V W-CDMA US-Cellular Handset
- 3V CDMA2000/1X-EV-DO US-Cellular Handset
- Spread-Spectrum System

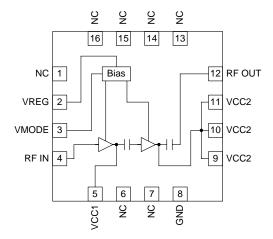
Product Description

The RF3163 is a high-power, high-efficiency linear amplifier module specifically designed for 3V handheld systems. The device is manufactured on an advanced third generation GaAs HBT process, and was designed for use as the final RF amplifier in 3V IS-95/CDMA2000-1X/AMPS/W-CDMA handheld digital cellular equipment, spread-spectrum systems, and other applications in the 824MHz to 849MHz band. The RF3163 has a digital control line for low power applications to lower quiescent current. The RF3163 is assembled in a 16-pin, 3mmx3mm, QFN package.



Optimum Technology Matching® Applied

☐ Si BJT ☐ GaAs MESFET☐ Si Bi-CMOS☐ SiGe HBT☐ Si CMOS☐ InGaP/HBT☐ GaN HEMT☐ SiGe Bi-CMOS☐



Functional Block Diagram

Package Style: QFN, 16-Pin, 3x3

Features

- Input Internally Matched @ 50Ω
- Output Internally Matched
- 28dBm Linear Output Power
- 41% Peak Linear Efficiency CDMA
- -51 dBc ACPR @ 885kHz
- 55% AMPS Efficiency

Ordering Information

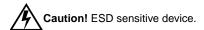
RF3163 3V 900MHz Linear Power Amplifier Module RF3163PCBA-41XFully Assembled Evaluation Board

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RF3163

Absolute Maximum Ratings

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Parameter	Rating	Unit			
Supply Voltage (RF off)	+8.0	V			
Supply Voltage (P _{OUT} ≤31dBm)	+5.2	V			
Control Voltage (V _{REG})	+3.9	V			
Input RF Power	+10	dBm			
Mode Voltage (V _{MODE})	+3.9	V			
Operating Temperature	-30 to +110	℃			
Storage Temperature	-40 to +150	°C			
Moisture Sensitivity Level (IPC/JEDEC J-STD-20)	MSL 2 @ 260℃				



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Parameter	Specification		Unit	Condition			
Farameter	Min.	Тур.	Max.	Unit	Condition		
High Power Mode - CDMA (V _{MODE} Low)					T=25°C Ambient, V _{CC} =3.4V, V _{REG} =2.8V, V _{MODE} =0V, and P _{OUT} =28dBm for all parameters (unless otherwise specified).		
Operating Frequency Range	824		849	MHz			
Linear Gain	26.0	28.5		dB			
Second Harmonics		-35	-30	dBc			
Third Harmonics		-40	-30	dBc			
Maximum Linear Output	28						
Linear Efficiency	37	41		%			
Maximum I _{CC}		455	501	mA			
ACPR @ 885kHz		-51	-46	dBc			
ACPR @ 1.98MHz		-58	-55	dBc			
Input VSWR		2:1					
Stability in Band			6:1		No oscillation>-70dBc		
Stability out of Band			10:1		No damage		
Noise Power		-133		dBm/Hz	At 45MHz offset.		
Low Power Mode - CDMA (V _{MODE} High)					T=25°C Ambient, V _{CC} =3.4V, V _{REG} =2.8V, V _{MODE} =2.8V, and P _{OUT} =18dBm for all parameters (unless otherwise specified).		
Operating Frequency Range	824		849	MHz			
Linear Gain	21	24		dB			
Maximum Linear Output	18						
Maximum I _{CC}		125	156	mA	P _{OUT} =16dBm		
ACPR @885kHz		-51	-46	dBc			
ACPR @1.98MHz		-61	-56	dBc			
Input VSWR		2:1					
Output VSWR Stability			6:1		No oscillation>-70dBc		
			10:1		No damage		

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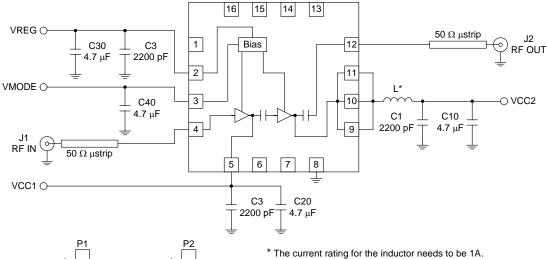
Danassatas	Specification			l lmi4	O a malitica m		
Parameter	Min.	Тур.	Max.	Unit	Condition		
High Power Mode -					T=25°C Ambient, V _{CC} =3.4V, V _{REG} =2.8V,		
W-CDMA (V _{MODE} Low)					V _{MODE} =0 V, and P _{OUT} =28 dBm for all parameters (unless otherwise specified).		
Operating Frequency Range	824		849	MHz			
Linear Gain		28.5		dB			
Maximum Linear Output	28	45		0/			
Linear Efficiency		45		% ^			
Maximum I _{CC}		410		mA			
ACLR @ 5MHz ACLR @ 10MHz		-41 -55		dBc dBc			
		33		abo	T=25°C Ambient, V _{CC} =3.4V, V _{REG} =2.8V,		
Low Power Mode -					V _{MODE} =2.8V, and P _{OUT} =18dBm for all		
W-CDMA (V _{MODE} High)					parameters (unless otherwise specified).		
Operating Frequency Range	824		849	MHz	, ,		
Linear Gain		24		dB			
Maximum Linear Output	18						
Maximum I _{CC}		120		mA	P _{OUT} =16dBm		
ACLR @ 5MHz		-41		dBc			
ACLR @ 10MHz		-60		dBc			
ENA NA o do					T=25°C Ambient, V_{CC} =3.4V, V_{REG} =2.8V,		
FM Mode					V _{MODE} =0 V, and P _{OUT} =31dBm for all		
On another Francisco Bound	004		0.40	N41.1-	parameters (unless otherwise specified).		
Operating Frequency Range	824	31	849	MHz dBm			
AMPS Maximum Output Power AMPS Efficiency	48	55		иБП %			
AMPS Gain	25.5	28		70			
AMPS Second Harmonics	20.0	-35	-30	dBc			
AMPS Third Harmonics		-40	-30	dBc			
Power Supply							
Supply Voltage	3.2	3.4	4.2	V			
High Gain Idle Current	ļ	55	80	mA	V _{MODE} =low and V _{REG} =2.8V		
Low Gain Idle Current		45	70	mA	V _{MODE} =high and V _{REG} =2.8V		
V _{REG} Current		4.5	5.5	mA	V _{MODE} =high		
V _{MODE} Current		250	1000	uA			
RF Turn On/Off Time			6	uS			
DC Turn On/Off Time			40	uS			
Total Current (Power Down)		0.2	2.0	uA			
V _{REG} Low Voltage	0		0.5	V			
V _{REG} High Voltage (Recommended)	2.75	2.8	2.95	V			
V _{REG} High Voltage (Operational)	2.7		3.0	V			
V _{MODE} Voltage	0		0.5	V	High Gain Mode		
	2.0		3.0	V	Low Gain Mode		

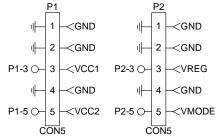
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Pin	Function	Description	Interface Schematic
1	NC	No connection. Do not connect this pin to any external circuit.	
2	VREG	Regulated voltage supply for amplifier bias circuit. In power down mode, both V_{REG} and V_{MODE} need to be LOW (<0.5 V).	
3	VMODE	For nominal operation (High Power mode), V _{MODE} is set LOW. When set HIGH, devices are biased lower to improve efficiency.	
4	RF IN	RF input internally matched to 50Ω . This input is internally AC-coupled.	
5	VCC1	First stage collector supply. A 2200pF and 4.7 μF decoupling capacitor are required.	
6	NC	No connection. Do not connect this pin to any external circuit.	
7	NC	No connection. Do not connect this pin to any external circuit.	
8	GND	Ground connection.	
9	VCC2	Output stage collector supply. Please see the schematic for required external components.	
10	VCC2	Same as pin 9.	
11	VCC2	Same as pin 9.	
12	RF OUT	RF output. Internally AC-coupled.	
13	NC	No connection. Do not connect this pin to any external circuit.	
14	NC	No connection. Do not connect this pin to any external circuit.	
15	NC	No connection. Do not connect this pin to any external circuit.	
16	NC	No connection. Do not connect this pin to any external circuit.	
Pkg Base	GND	Ground connection. The backside of the package should be soldered to a top side ground pad which is connected to the ground plane with multiple vias. The pad should have a short thermal path to the ground plane.	

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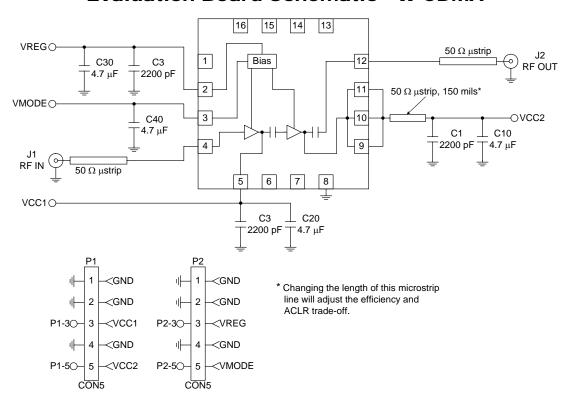
Evaluation Board Schematic - CDMA





* The current rating for the inductor needs to be 1A. One example is Toko 0603 multilayer inductor with the value of 1.8 nH (Toko part number LL1608-F1N8S). The value of the inductor can be from 1.5nH to 2.2nH. Different values of the inductor will give slight shift on the tradeoff between efficiency and ACPR.

Evaluation Board Schematic - W-CDMA



Electrostatic Discharge Sensitivity

Human Body Model (HBM)

Figure 3 shows the HBM ESD sensitivity level for each pin to ground. The ESD test is in compliance with JESD22-A114.

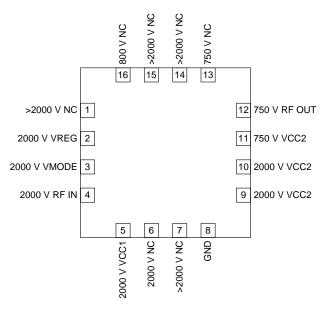


Figure 3. ESD Level - Human Body Model

Machine Model (MM)

Figure 4 shows the MM ESD sensitivity level for each pin to ground. The ESD test is in compliance with JESD22-A115.

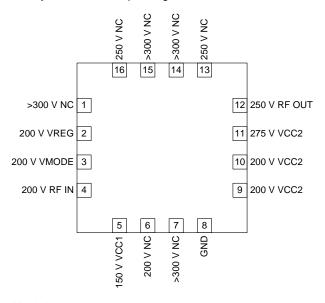


Figure 4. ESD Level - Machine Model

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PCB Design Requirements

PCB Surface Finish

The PCB surface finish used for RFMD's qualification process is electroless nickel, immersion gold. Typical thickness is 3µinch to 8µinch gold over 180µinch nickel.

PCB Land Pattern Recommendation

PCB land patterns for PFMD components are based on IPC-7351 standards and RFMD empirical data. The pad pattern shown has been developed and tested for optimized assembly at RFMD. The PCB land pattern has been developed to accommodate lead and package tolerances. Since surface mount processes vary from company to company, careful process development is recommended.

PCB Metal Land Pattern

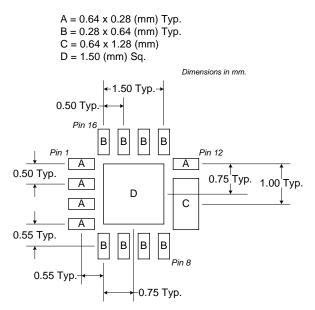


Figure 1. PCB Metal Land Pattern (Top View)

PCB Solder Mask Pattern

Liquid Photo-Imageable (LPI) solder mask is recommended. The solder mask footprint will match what is shown for the PCB metal land pattern with a 2mil to 3mil expansion to accommodate solder mask registration clearance around all pads. The center-grounding pad shall also have a solder mask clearance. Expansion of the pads to create solder mask clearance can be provided in the master data or requested from the PCB fabrication supplier.

 $A = 0.74 \times 0.38$ (mm) Typ. $B = 0.38 \times 0.74 \text{ (mm) Typ.}$ C = 1.60 (mm) Sq.Dimensions in mm ←1.50 Typ.÷ 0.50 Typ Pin 16 В В В В Pin 12 Pin Α Α 0.50 Typ. 0.75 Α Α С 1.50 Typ. Α Α Α Α 0.55 Typ. В В В В Pin 8 0.55 Typ. -0.75

Figure 2. PCB Solder Mask Pattern (Top View)

Thermal Pad and Via Design

The PCB land pattern has been designed with a thermal pad that matches the die paddle size on the bottom of the device.

Thermal vias are required in the PCB layout to effectively conduct heat away from the package. The via pattern has been designed to address thermal, power dissipation and electrical requirements of the device as well as accommodating routing strategies.

The via pattern used for the RFMD qualification is based on thru-hole vias with 0.203mm to 0.330mm finished hole size on a 0.5mm to 1.2mm grid pattern with 0.025mm plating on via walls. If micro vias are used in a design, it is suggested that the quantity of vias be increased by a 4:1 ratio to achieve similar results.

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Tape and Reel Information

Carrier tape basic dimensions are based on EIA481. The pocket is designed to hold the part for shipping and loading onto SMT manufacturing equipment, while protecting the body and the solder terminals from damaging stresses. The individual pocket design can vary from vendor to vendor, but width and pitch will be consistent.

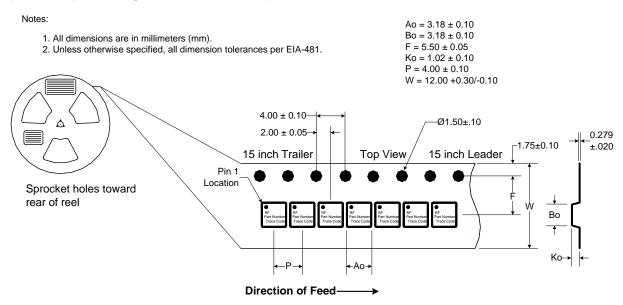
Carrier tape is wound or placed onto a shipping reel either 330 mm (13 inches) in diameter or 178 mm (7 inches) in diameter. The center hub design is large enough to ensure the radius formed by the carrier tape around it does not put unnecessary stress on the parts.

Prior to shipping, moisture sensitive parts (MSL level 2a-5a) are baked and placed into the pockets of the carrier tape. A cover tape is sealed over the top of the entire length of the carrier tape. The reel is sealed in a moisture barrier, ESD bag, which is placed in a cardboard shipping box. It is important to note that unused moisture sensitive parts need to be resealed in the moisture barrier bag. If the reels exceed the exposure limit and need to be rebaked, most carrier tape and shipping reels are not rated as bakeable at 125°C. If baking is required, devices may be baked according to section 4, table 4-1, column 8 of Joint Industry Standard IPC/JEDEC J-STD-033A.

The following table provides useful information for carrier tape and reels used for shipping the devices described in this document.

RFMD Part Number	Reel Diameter Inch (mm)	Hub Diameter Inch (mm)	Width (mm)	Pocket Pitch (mm)	Feed	Units per Reel
RF3163TR7	7 (178)	2.4 (61)	12	4	Single	2500

QFN (Carrier Tape Drawing with Part Orientation)



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